



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = 25°C		
60V	7.5Ω @ $V_{GS} = 5V$	0.23A		

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2 and 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

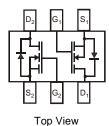
- Motor control
- Power Management Functions

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



Top View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002DW-7-F	SOT363	3,000/Tape & Reel
2N7002DW-13-F	SOT363	10,000/Tape & Reel

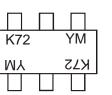
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

3. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K72 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

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Year	1998	1999	2000	2001	2002	2003	2004		2011	2012	2013	2014	2015	2016	2017
Code	J	K	L	М	N	Р	R		Y	Z	А	В	С	D	E
Month	Jan	Fe	b I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t I	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		VDSS	60	V	
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$		V _{DGR}	60	V	
Cata Source Valtage	Continuo	us	V _{GSS}	±20	V
Gate-Source Voltage	Pulsed		V _{GSS}	±40	V
pontinuous Drain Current (Note 6) $V_{GS} = 5V$ Steady $T_A = 70^{\circ}C$		$T_A = 25^{\circ}C$ $T_A = 70^{\circ}C$ $T_A = 100^{\circ}C$	ID	0.23 0.18 0.14	A
Maximum Continuous Body Diode Forward Curre	nt (Note 6)	Is	0.53	А	
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)	I _{DM}	0.8	А	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units		
	T _A = 25°C		0.31		
Total Power Dissipation (Note 5)	$T_A = 70^{\circ}C$	PD	0.2	W	
	$T_A = 100^{\circ}C$		0.12		
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{ ext{ heta}JA}$	410	°C/W	
	T _A = 25°C		0.4		
Total Power Dissipation (Note 6)	$T_A = 70^{\circ}C$	PD	0.25	W	
	T _A = 100°C		0.15		
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{ ext{ heta}JA}$	318	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady state	R ₀ JC	135	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	IDSS	_	—	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = 25°C	Pro (ou)	_	3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
	@ T _J = 125°C	R _{DS} (ON)		4.4	13.5		$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0		Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		g fs	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage		V _{SD}	_	0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		Ciss	_	22	50	pF	
Output Capacitance	Output Capacitance		_	11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		Crss		2.0	5.0	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time		t _{D(on)}	_	7.0	20		$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(off)}	_	11.0	20	ns	$\begin{aligned} R_L &= 150\Omega, \ V_GEN = 10V, \\ R_GEN &= 25\Omega \end{aligned}$

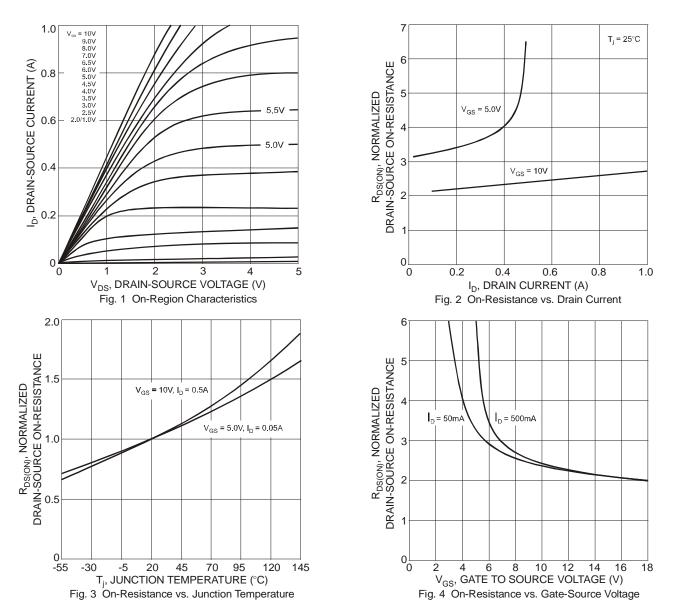
Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
Short duration pulse test used to minimize self-heating effect.

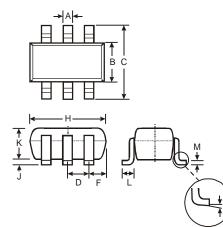
8. Guaranteed by design. Not subject to product testing.

2N7002DW





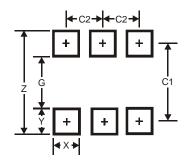
Package Outline Dimensions



SOT363						
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65	Тур				
F	0.40	0.45				
Н	1.80	2.20				
J	0	0.10				
κ	0.90	1.00				
L	0.25	0.40				
М	0.10	0.22				
α 0° 8°						
All Di	mensions	in mm				



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

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